EMH3FHA / UMH3NFHA / IMH3AFRA

NPN 100mA 50V Complex Digital Transistors (Bias Resistor Built-in Transistors) Datasheet

AEC-Q101 Qualified

Parameter	Tr1 and Tr2
V _{CEO}	50V
I _{C(MAX.)}	100mA
R ₁	4.7kΩ

Features

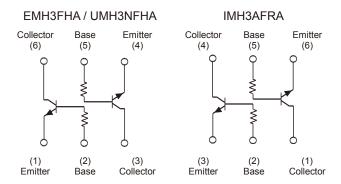
- 1) Built-In Biasing Resistors.
- 2) Two DTC143T chips in one package.
- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 5) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 6) Lead Free/RoHS Compliant.

Application

Inverter circuit, Interface circuit, Driver circuit

●Outline	
EMT6	UMT6
$(1) \underbrace{(2)}_{(2)}^{(6)}_{(3)}^{(5)}_{(4)}$	$(1)_{(2)}_{(3)}^{(6)}_{(5)}^{(5)}(4)$
EMH3FHA (SC-107C)	UMH3NFHA SOT-353 (SC-88)
SMT6 (3)(2)(1) ⁽⁴⁾⁽⁵⁾ (6)	
IMH3AFRA SOT-457 (SC-74)	

Inner circuit



Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
EMH3FHA	EMT6	1616	T2R	180	8	8,000	H3
UMH3NFHA	UMT6	2021	TR	180	8	3,000	H3
IMH3AFRA	SMT6	2928	T108	180	8	3,000	H3

•Absolute maximum ratings (Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter		Symbol	Values	Unit
Collector-base voltage		V _{CBO}	50	V
Collector-emitter voltage		V _{CEO}	50	V
Emitter-base voltage		V_{EBO}	5	V
Collector current		۲ _{C(MAX.)} *1	100	mA
Collector Power dissipation	EMH3FHA / UMH3NFHA	P _D ^{*2}	150 (Total) ^{*3}	mW
IMH3AFRA		PD	300 (Total) ^{*4}	mW
Junction temperature		Τ _j	150	°C
Range of storage temperature		T _{stg}	–55 to +150	°C

•Electrical characteristics(Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV_{CBO}	I _C = 50μA	50	-	-	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = 1mA	50	-	-	V
Emitter-base breakdown voltage	BV_{EBO}	I _E = 50μA	5	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} = 50V	-	-	0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 4V	-	-	0.5	μA
Collector-emitter saturation voltage	V _{CE(sat)}	I _C / I _B = 5mA / 0.25mA	-	-	0.15	V
DC current gain	h _{FE}	V_{CE} = 5V , I _C = 1mA ,	100	250	600	-
Input resistance	R ₁	-	3.5	4.7	5.9	kΩ
Transition frequency	f _T *1	V _{CE} = 10V, I _E = -5mA, f = 100MHz	-	250	-	MHz

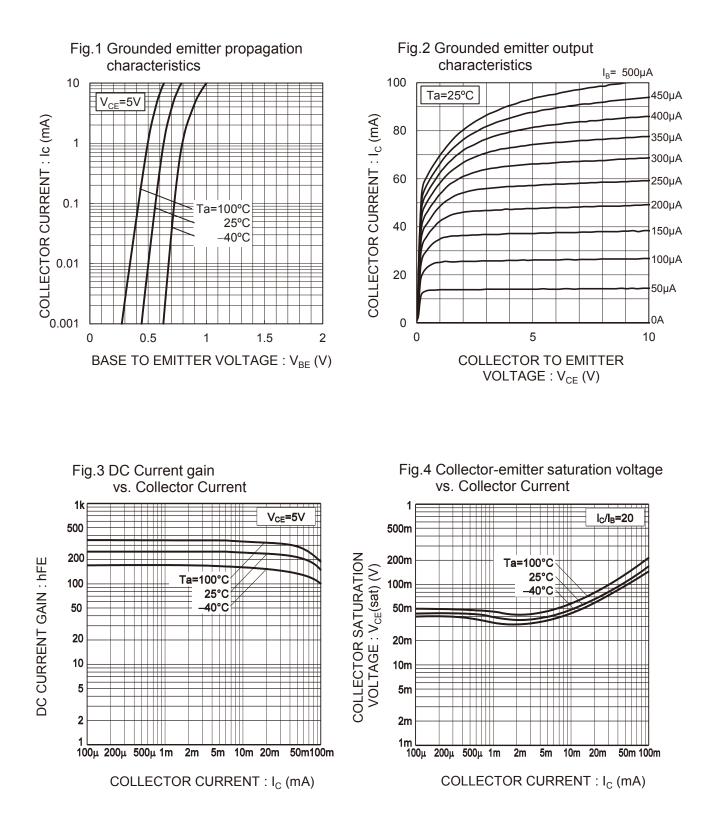
*1 Characteristics of built-in transistor

*2 Each terminal mounted on a reference footprint

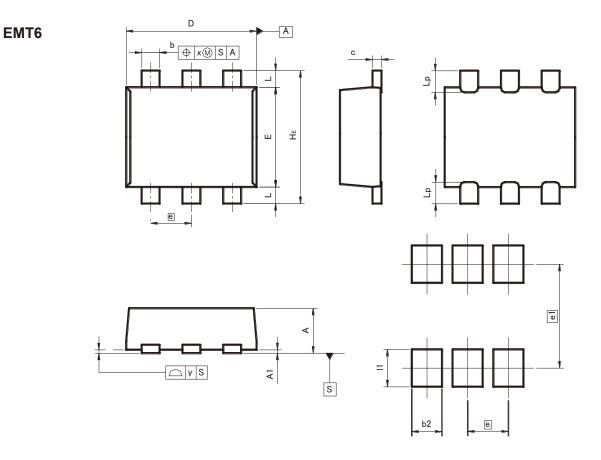
*3 120mW per element must not be exceeded.

*4 200mW per element must not be exceeded.

•Electrical characteristic curves(Ta = 25°C)



•Dimensions (Unit : mm)



Patterm of terminal position areas

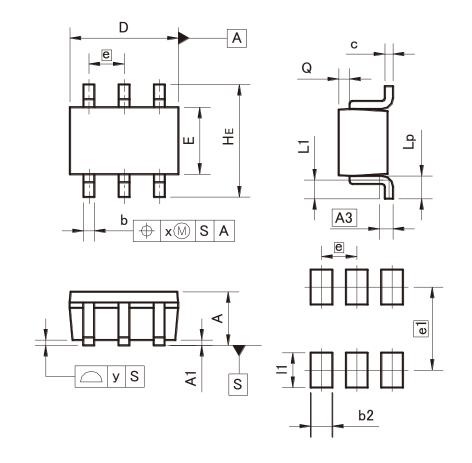
DIM	MILIM	ETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
A1	0.00	0.10	0	0.004	
Α	0.45	0.55	0.018	0.022	
b	0.17	0.27	0.007	0.011	
с	0.08	0.18	0.003	0.007	
D	1.50	1.70	0.059	0.067	
E	1.10	1.30	0.043	0.051	
е	0.	50	0.02		
HE	1.50	1.70	0.059	0.067	
L	0.10	0.30	0.004	0.012	
Lp	-	0.35	-	0.014	
x	_	0.10	_	0.004	
У	_	0.10	_	0.004	

DIM	MILIMETERS		MILIMETERS INCHES		
DIM	MIN	MAX	MIN	MAX	
e1	1.25		0.049		
b2	-	0.37	-	0.015	
1	-	0.45	-	0.018	

Dimension in mm/inches

•Dimensions (Unit : mm)

UMT6



Patterm of terminal position areas

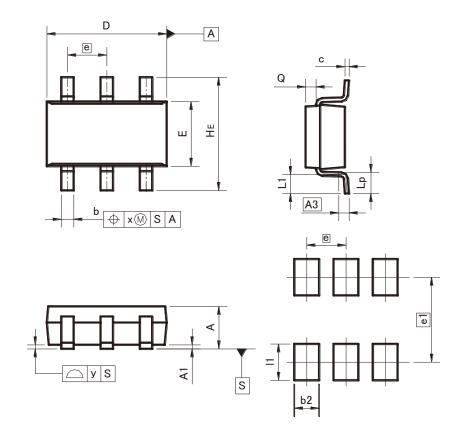
DIM	MILIM	ETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
А	0.80	1.00	-	0.039	
A1	0.00	0.10	0	0.004	
A3	0.1	25	0.0	01	
b	0.15	0.30	0.006	0.012	
с	0.10	0.20	0.004	0.008	
D	1.90	2.10	0.075	0.083	
E	1.15	1.35	0.045	0.053	
е	0.	65	0.03		
HE	2.00	2.20	0.079	0.087	
L1	0.20	0.50	0.008	0.02	
Lp	0.25	0.55	0.01	0.022	
Q	0.10	0.30	0.004	0.012	
х	_	0.10	_	0.004	
У	_	0.10	_	0.004	

DIM	MILIMETERS		MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX		
e1	1.55		0.06			
b2	-	0.40	-	0.016		
1	-	0.65	-	0.026		

Dimension in mm/inches

•Dimensions (Unit : mm)

SMT6



Patterm of terminal position areas

DIM	MILIM	ETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
А	1.00	1.30	0.039	0.051	
A1	0.00	0.10	0	0.004	
A3	0.1	25	0.0	01	
b	0.25	0.40	0.01	0.016	
С	0.09	0.25	0.004	0.01	
D	2.80	3.00	0.11	0.118	
E	1.50	1.80	0.059	0.071	
е	0.9	95	0.04		
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.20	0.30	0.008	0.012	
x	_	0.20	_	0.008	
У	_	0.10	_	0.004	

DIM	MILIMETERS		MILIMETERS INCHES		
DIN	MIN	MAX	MIN	MAX	
e1	2.10		0.08		
b2		0.60	-	0.024	
1	-	0.90	-	0.035	

Dimension in mm/inches

	Notes
	or reproduction of this document, in part or in whole, is permitted without the OHM Co.,Ltd.
The content	specified herein is subject to change for improvement without notice.
"Products").	specified herein is for the purpose of introducing ROHM's products (hereinafte If you wish to use any such Product, please be sure to refer to the specifications e obtained from ROHM upon request.
illustrate the	application circuits, circuit constants and any other information contained hereir standard usage and operations of the Products. The peripheral conditions mus account when designing circuits for mass production.
However, sh	vas taken in ensuring the accuracy of the information specified in this document ould you incur any damage arising from any inaccuracy or misprint of such ROHM shall bear no responsibility for such damage.
examples of implicitly, any other parties	I information specified herein is intended only to show the typical functions of and application circuits for the Products. ROHM does not grant you, explicitly of y license to use or exercise intellectual property or other rights held by ROHM and B. ROHM shall bear no responsibility whatsoever for any dispute arising from the rechnical information.
equipment o	s specified in this document are intended to be used with general-use electronic r devices (such as audio visual equipment, office-automation equipment, commu- ces, electronic appliances and amusement devices).
The Product	s specified in this document are not designed to be radiation tolerant.
	1 always makes efforts to enhance the quality and reliability of its Products, a fail or malfunction for a variety of reasons.
against the p failure of any shall bear no	The to implement in your equipment using the Products safety measures to guard cossibility of physical injury, fire or any other damage caused in the event of the Product, such as derating, redundancy, fire control and fail-safe designs. ROHM presponsibility whatsoever for your use of any Product outside of the prescribed in accordance with the instruction manual.
system whic may result in instrument, to controller or of the Produ	s are not designed or manufactured to be used with any equipment, device on h requires an extremely high level of reliability the failure or malfunction of which a direct threat to human life or create a risk of human injury (such as a medica ransportation equipment, aerospace machinery, nuclear-reactor controller, fuel- other safety device). ROHM shall bear no responsibility in any way for use of any locts for the above special purposes. If a Product is intended to be used for any purpose, please contact a ROHM sales representative before purchasing.
be controlled	to export or ship overseas any Product or technology specified herein that may d under the Foreign Exchange and the Foreign Trade Law, you will be required to use or permit under the Law.



Thank you for your accessing to ROHM product informations. More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/